

TO-92L Plastic-Encapsulate Transistors

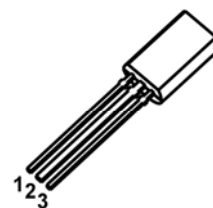
2SB562 TRANSISTOR (PNP)

FEATURES

- Low Frequency Power Amplifier
- Complementary Pair with 2SD468

TO - 92L

1. EMITTER
2. COLLECTOR
3. BASE



MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector-Base Voltage	-25	V
V _{CEO}	Collector-Emitter Voltage	-20	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current	-1	A
P _C	Collector Power Dissipation	750	mW
R _{θJA}	Thermal Resistance From Junction To Ambient	167	°C/W
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55~+150	°C

ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-10μA, I _E =0	-25			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-1mA, I _B =0	-20			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-10μA, I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} =-20V, I _E =0			-1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-4V, I _C =0			-1	μA
DC current gain	h _{FE} *	V _{CE} =-2V, I _C =-0.5A	85		240	
Collector-emitter saturation voltage	V _{CE(sat)} *	I _C =-0.8A, I _B =-0.08A			-0.5	V
Base-emitter voltage	V _{BE} *	V _{CE} =-2V, I _C =-0.5A			-1	V
Collector output capacitance	C _{ob}	V _{CB} =-10V, I _E =0, f=1MHz		38		pF
Transition frequency	f _T	V _{CE} =-2V, I _C =-0.5A		350		MHz

*Pulse test

CLASSIFICATION OF h_{FE}

RANK	B	C
RANGE	85-170	120-240